

SSCP006GSB

High Frequency High Gain PNP Power BJT

Features

VCE	VBE	VCESAT Typ.	IC
-40V	-8V	-150mV	-1.2A

> Description

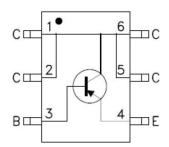
This device is produced with advanced high carrier density technology, which is especially used to minimize saturation voltage drop. This device particularly suits low voltage applications such as portable equipment, power management and other battery powered circuits, and low in-line power dissipation are needed in a very small outline surface mount package. Excellent thermal and electrical capabilities.

Applications

- Battery powered circuits
- Low in-line power dissipation circuits
- Power regulator

> Pin configuration

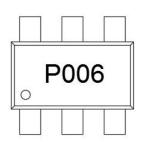
Top view



SOT23-6L



Bottom view



> Ordering Information

Device	Package	Shipping
SSCP006GSB	SOT23-6L	3000/Reel



➤ Absolute Maximum Ratings(T_A=25°C unless otherwise specified)

Symbol	Parameter	Ratings	Unit	
V _{CBO}	Collector-Base Voltage	-50	V	
V _{CEO}	Collector-Emitter Voltage	-40	V	
V_{EBO}	Emitter-Base Voltage	-8	V	
ı	Collector Current@Note1		^	
IC	Collector Current@Note2	-1	Α	
I _{CM}	Pulsed Collector Current@Note3	-4	Α	
Б	Power Dissipation@Note1	1.2	10/	
P_{D}	Power Dissipation@Note2	0.8	W	
T _A	Operation Temperature Range	-40 to 85	°C	
TL	Lead Temperature	260	°C	
T_J, T_STG	Operation and Storage temperature range	-55 to 150	°C	

> Thermal Resistance Ratings

Symbol	Parameter	Maximum	Unit
R _{0JA}	Junction-to-Ambient Thermal	110	°C/W
	Resistance@Note1	119	
R _{0JA}	Junction-to-Ambient Thermal		
	Resistance@Note2	166	



➤ Electronics Characteristics(T_A=25°C unless otherwise specified)

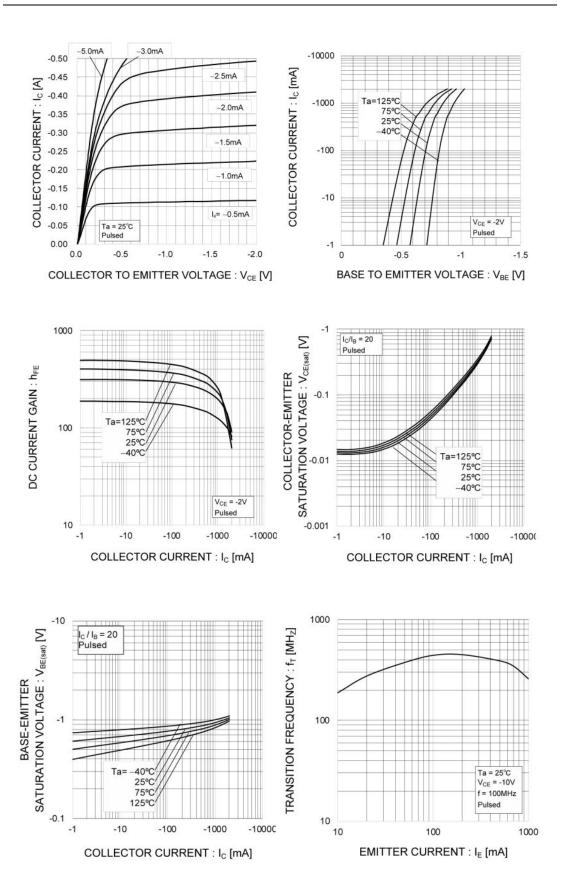
Symbol	Parameter	Test Conditions	Min	Тур.	Max	Unit
BVCBO	Collector-Base	IC=-0.1mA	-50			V
ВУСВО	Breakdown Voltage	IE=0	-50			V
BVCEO	Collector-Emitter	IC=-1mA	-40			\ \
BVCLO	Breakdown Voltage	IB=0	-40			V
BVEBO	Emitter-Base	IE=-0.1mA	0	-8		V
BVEBO	Breakdown Voltage	IC=0	-0			V
ICBO	Collector cut off	VCB=-35V		-0.1	0.1	uA
ЮВО	current	IE=0			-0.1	
IEBO	Emitter cut off	VEB=-4V			-0.1	uА
IEBO	current	IC=0			-0.1	uA
HFE	DC Current	VCE=-1V	200 2	250	350	
	Gain@Note3	IC=-0.1A	200	250	330	
VCESAT	Collector-Emitter	IC=-0.8A		-0.15	-0.25	V
VCESAI	Saturation Voltage	IB=-80mA		-0.13	-0.23	V
VBESAT	Base-Emitter	IC=-0.8A		-0.9	-1.2	V
VDESAI	Saturation Voltage	IB=-80mA		-0.9	-1.2	v
f⊤	Transition	VCE=-6V , IC=-20mA	150			MHz
IT IT	frequency	f=30MHz	130			IVI⊓∠

Notes:

- Surface mounted on FR-4 Board using 1 square inch pad size, 1oz copper.
- 2. Surface mounted on FR-4 Board using minimum pad size, 1oz copper.
- 3. Pulse width=300us, Duty Cycle<2%.

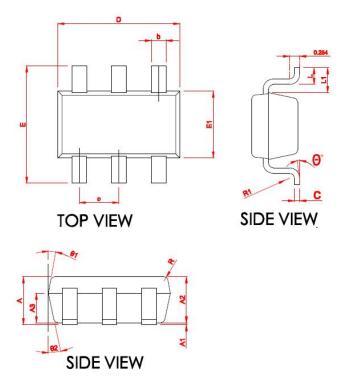
> Typical Performance Characteristics





Package Information





	MILLIMETER			
SYMBOL	MIN	NOM	MAX	
Α	1.06	1.15	1.24	
* A1	0.01	0.05	0.09	
* A2	1.05	1.10	1.15	
A3	0.65	0.70	0.75	
* b	0.30	0.35	0.45	
* c	0.117	0.127	0.157	
* D	2.87	2.92	2.97	
* E	2.72	2.80	2.88	
* E1	1.55	1.60	1.65	
* e	0.90	0.95	1.00	
* L	0.32	0.40	0.48	
* L1	0.55	0.60	0.65	
R	0.10 REF			
R1	0.12 REF			
* 0	0		8°	
θ1	8°	10°	12°	
θ2	10°	12°	14°	

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